

Simplified nonquasi-static FET modelling approach experimentally validated up to 118.5 GHz

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In this paper two similar simplified nonquasi-static approaches are applied for high-frequency large-signal FET prediction. Both account for low-frequency dispersion and use a simplified extraction process through the use of linear delays. Excellent results are obtained from dc up to the device $f_{\text{sub T}}$ frequencies, even when $f_{\text{sub T}}$ is 120 GHz. For low-frequency prediction a simple quasi-static extrinsic approach can produce excellent results thus further simplifying modelling. The influence of including the low-frequency dispersion modelling is also taken into account.

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